

Clean room analysis of the PMS150C programming sequence v0.3

Thanks to everyone involved in investigating the Padauk microcontrollers on the EEV and μ C.net forums. Please see here for further background and work leading to this analysis:

<http://www.eevblog.com/forum/blog/eevblog-1144-padauk-programmer-reverse-engineering/350/>

<https://www.mikrocontroller.net/topic/461002>

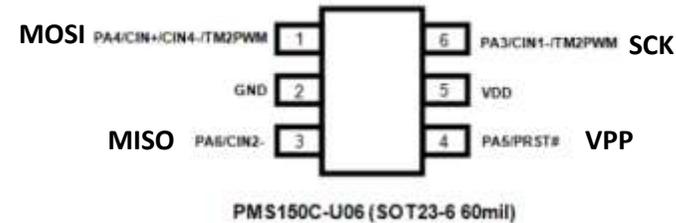
Clean Room Analysis Disclaimer

- This report is solely based on analyzing datalogs of the programming sequence as provided here: <http://www.eevblog.com/forum/blog/eevblog-1144-padauk-programmer-reverse-engineering/msg2096917/#msg2096917>
- No attempts have been made by me to reverse engineer any of the software provided by Padauk.
- The information in this document is provided “as is”, without warranty of any kind.
- No attempts have been made so far to verify any of the observations on actual hardware. Please update where necessary.

Initial analysis of data logs.

From a first glance, the programming interface of the PMS150C seems to be a straight forward SPI interface. MSB first, data is valid on rising edge of clk.

The pinout is as follows:



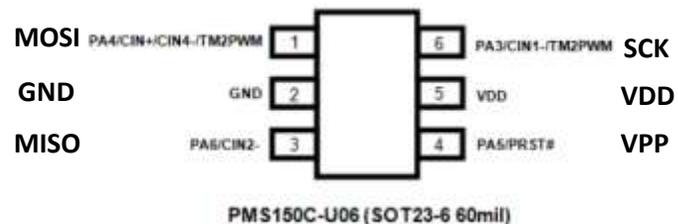
- PA3: SCK/Clock (driven by writer/master)
- PA4: MOSI/Data in (driven by writer/master, data is valid on rising edge of clk. Data is set at arbitrary times due to random timing of writer software)
- PA5: VPP
- PA6: MISO/Data out (driven by MCU, data is valid on rising edge of clk. Data is set on falling edge since the MCU does not have an internal clk)
- Furthermore, the programmer needs to control VDD to reset the MCU.

VPP is 7.5V during read and 10.8 V during writing.

VDD is 6.0 V during programming, 4 V during entry and 6.5 V/2 V for verification. It may be sufficient to keep VDD at 5V if you don't want to verify all corner cases.

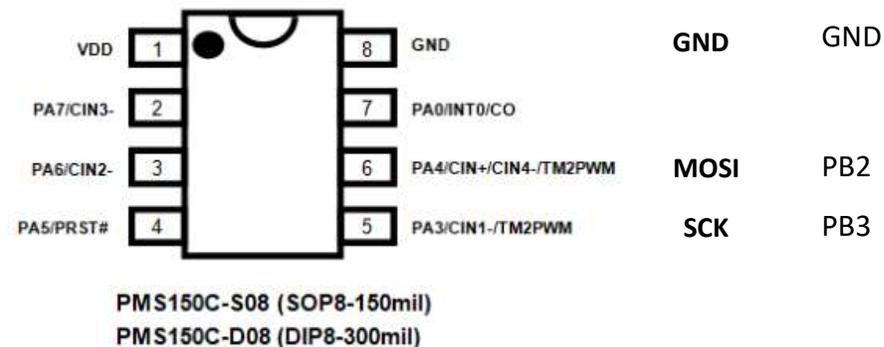
Note: The PMS105C is a device with 13x1kbit memory and 13 bit instruction encoding.

Pinouts

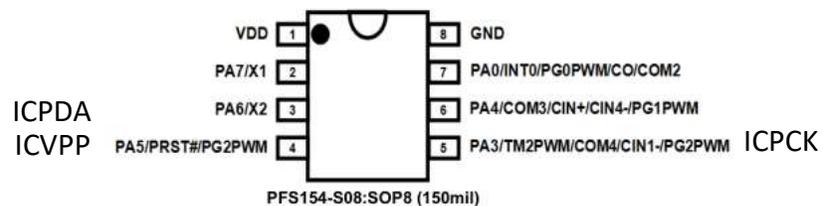


PB0
PB1
OC0A/D6

VDD
MISO
VPP

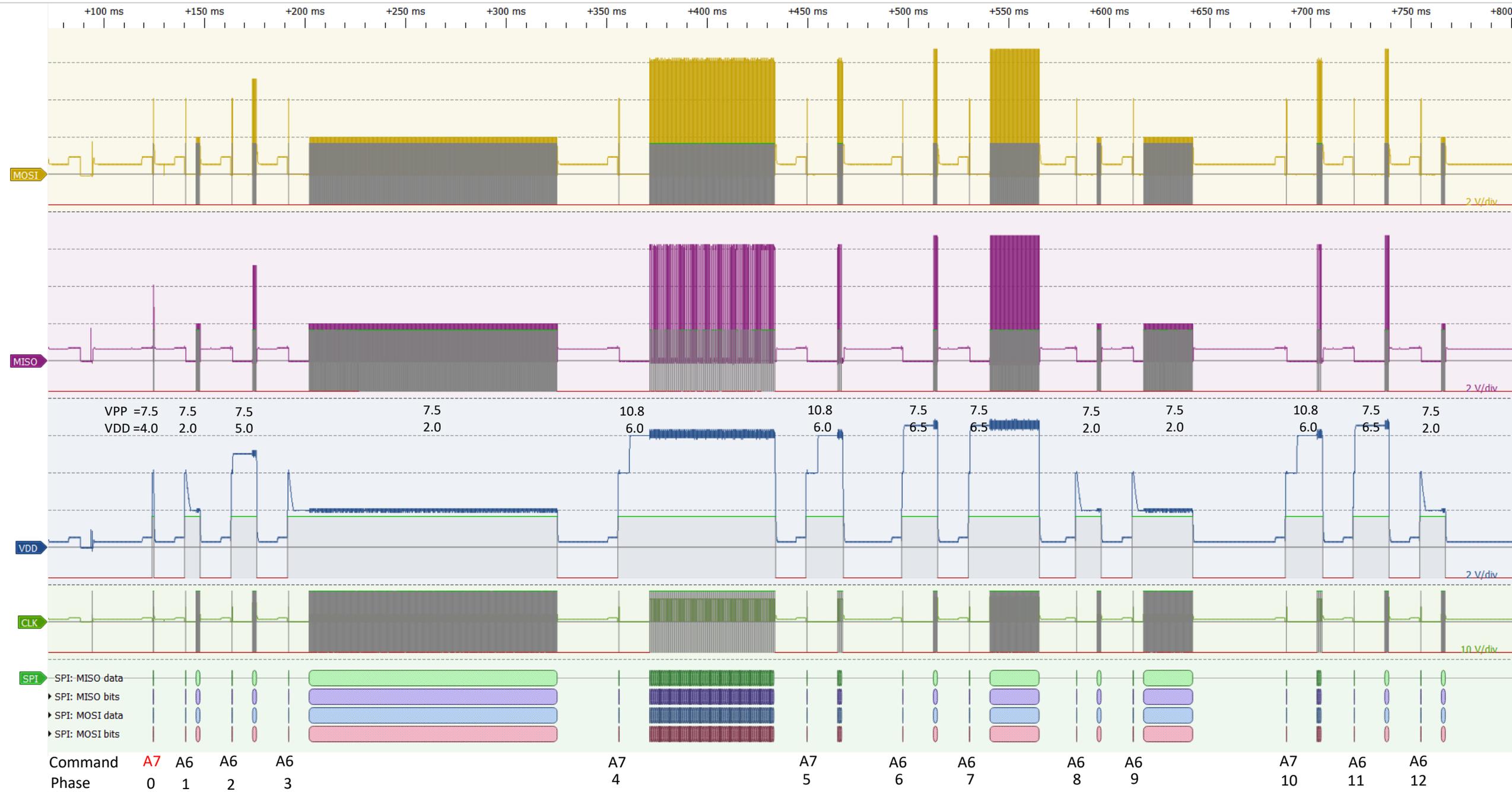


PFS154



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Overview of dump2 – writing to previously programmed device

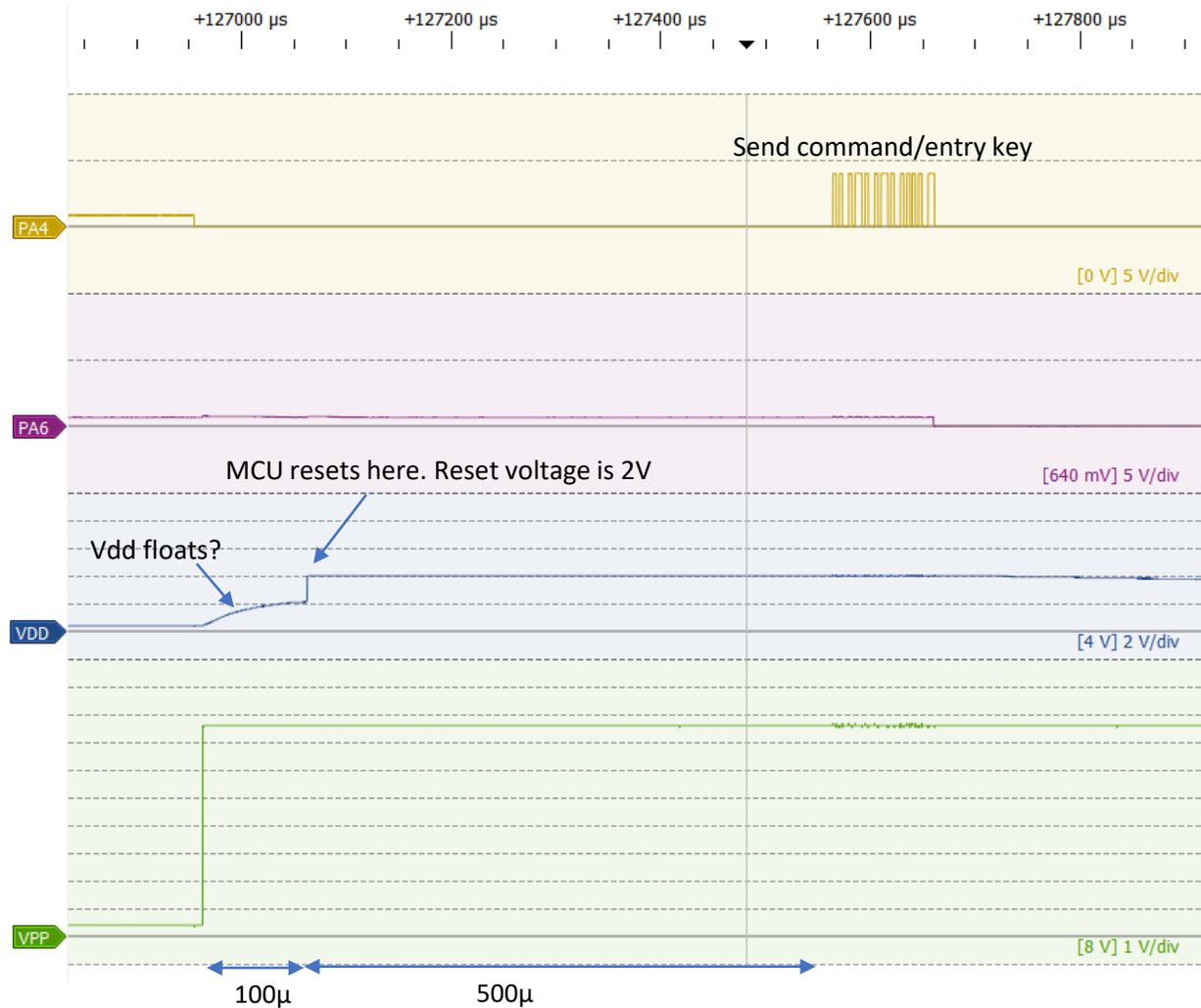


Summary of all phases of the programming sequence (Dump 2)

Phase	Command	VDD	VPP	Description
0	A7 (Write)	4.0 V	7.5 V	Read device ID. This is achieved by initiating a dummy write that is aborted before starting the actual OTP programming
1	A6 (Read)	2.0 V	7.5 V	Read instruction memory words 0x03F0-0x3FF at low VDD voltage corner. This region contains calibration data.
2	A6 (Read)	5.0 V	7.5 V	Read instruction memory words 0x03F0-0x3FF at standard voltage corner. This region contains calibration data. (Should this be VDD=6.5V? May be a bug)
3	A6 (Read)	2.0 V	7.5 V	Read instruction memory words 0x000-0x3EF at low VDD voltage corner. Dump of full memory.
4	A7 (Write)	6.0 V	10.8 V	Write main memory region between 0x000-0x3EF. Only memory cells used by the program are written to.
5	A7 (Write)	6.0 V	10.8 V	Write to 0x3F6/0x3F8/0x3FC/0x3FE. Housekeeping?
6	A6 (Read)	6.5 V	7.5 V	Read instruction memory words 0x03F0-0x3FF at high voltage corner for verification.
7	A6 (Read)	6.5 V	7.5 V	Read main memory region between 0x000-0x3EF at high voltage corner for verification. Only previously written memory is read.
8	A6 (Read)	2.0 V	7.5 V	Read instruction memory words 0x03F0-0x3FF at low voltage corner for verification.
9	A6 (Read)	2.0 V	7.5 V	Read main memory region between 0x000-0x3EF at low voltage corner for verification. Only previously written memory is read.
10	A7 (Write)	6.0 V	10.8 V	Write to 0x3F6/0x3F8/0x3FC/0x3FE to store clock calibration data and code checksum.
11	A6 (Read)	6.5 V	7.5 V	Read instruction memory words 0x03F0-0x3FF at high voltage corner for verification.
12	A6 (Read)	2.0 V	7.5 V	Read instruction memory words 0x03F0-0x3FF at low voltage corner for verification.

- Note: For a fresh device, clock calibration takes place between steps 9 and 10. Two additional phases are inserted (see dump 4).

Enter programming mode



Each phase of the programming sequence is as follows:

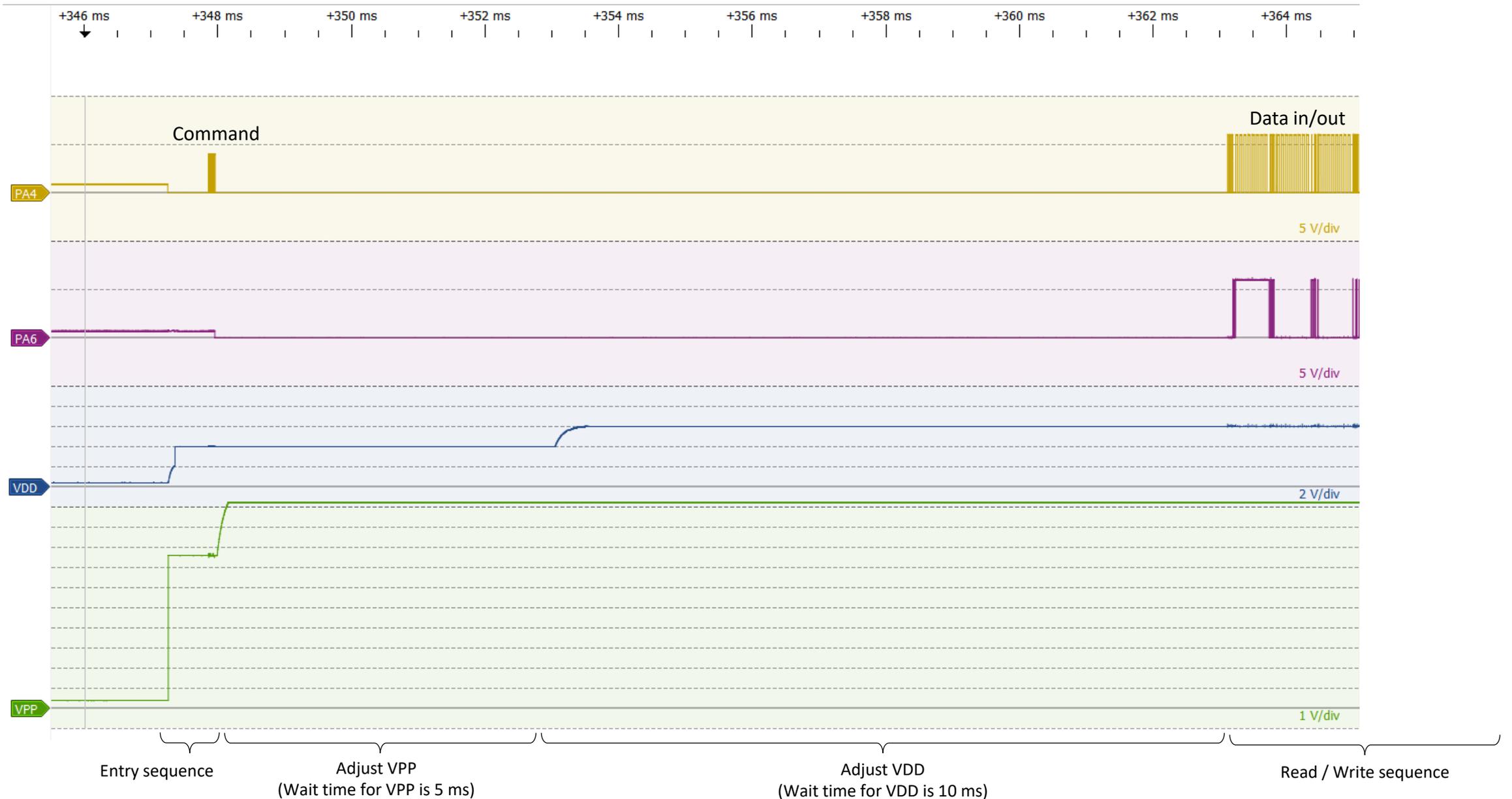
1. Set all pins to GND
2. Drive VPP to 7.5V (possibly >6V is threshold?)
3. wait 100μs
4. Drive VDD to ~4V
5. wait 500μs
6. Send key/command 0xA5A5A5AX (X=6 for read, X=7 for write)
7. Ramp to target VPP (7.5 V for reading, 10.8V for writing)
8. Wait for 5 ms
9. Ramp to target VDD
10. Wait for 10 ms
11. *Perform read or write operation (see later slides)*
12. Pull VDD and VPP to GND

Programming mode is always entered with
Vpp=7.5 V
Vdd=4 V

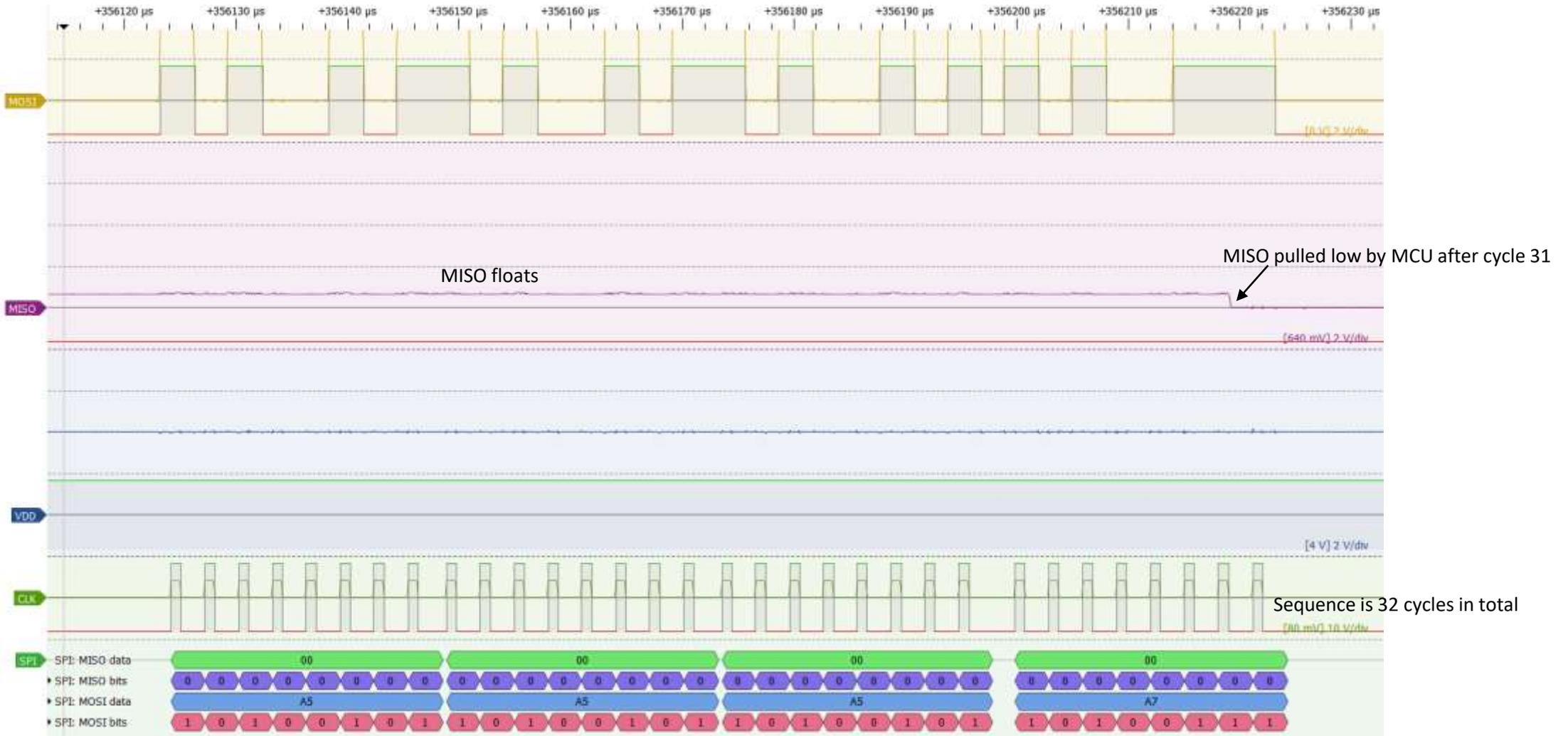
Voltages are only adjusted to final target after sending command (step 6).
Steps 7-10 can be skipped if initial voltages are kept.

Note: Logic levels scale with Vdd. If varying Vdd is implemented, this needs to be considered in the SPI interface hardware (buffer).

Enter programming mode with voltage adjustment and read/write phase

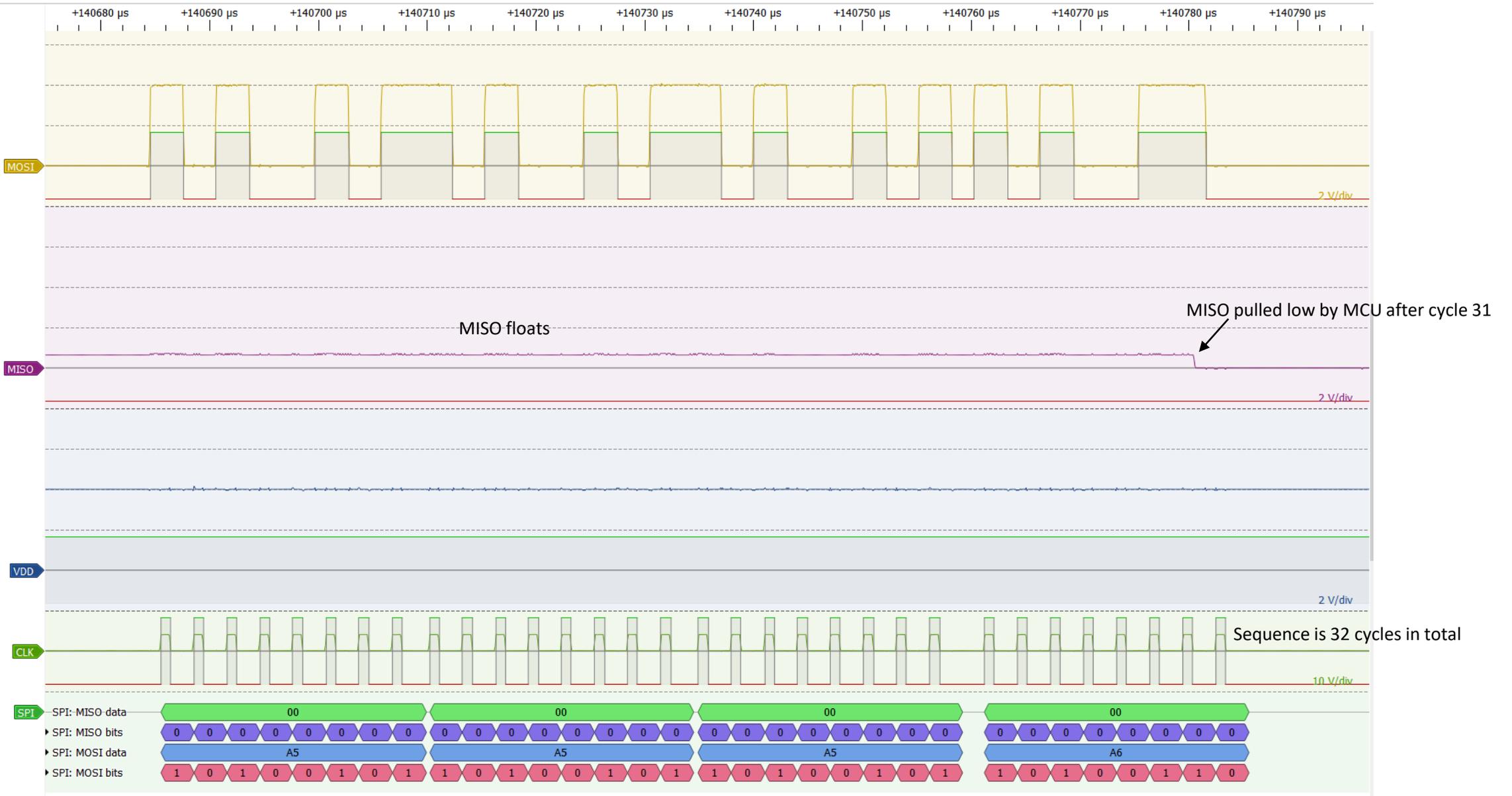


0xA5A5A5A7 key/command – write



Not on PulseView: SPI decoder uses VDD as CS (Active high). This will reset the bitcount when the MCU is reset and ensures proper decoding for magic word
Analog signal were converted to logic by using a threshold of 1.8V (3.3V logic) to also capture the regions with Vdd=2V

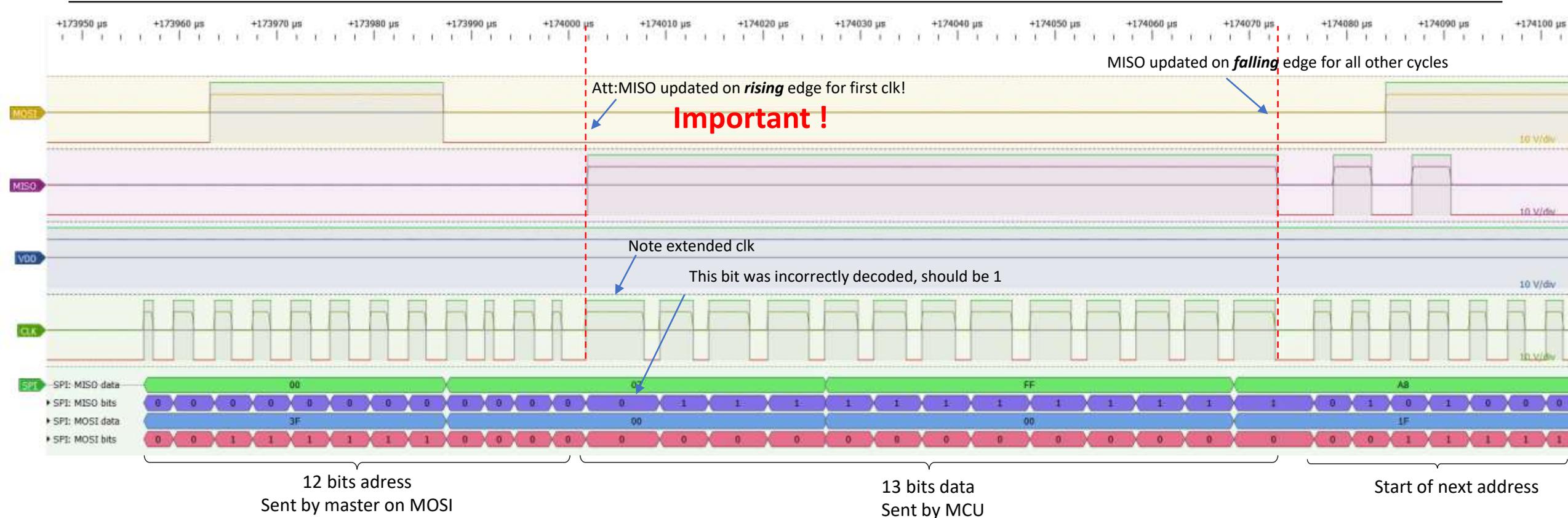
0xA5A5A5A6 key/command - read



Command / Entry key encoding

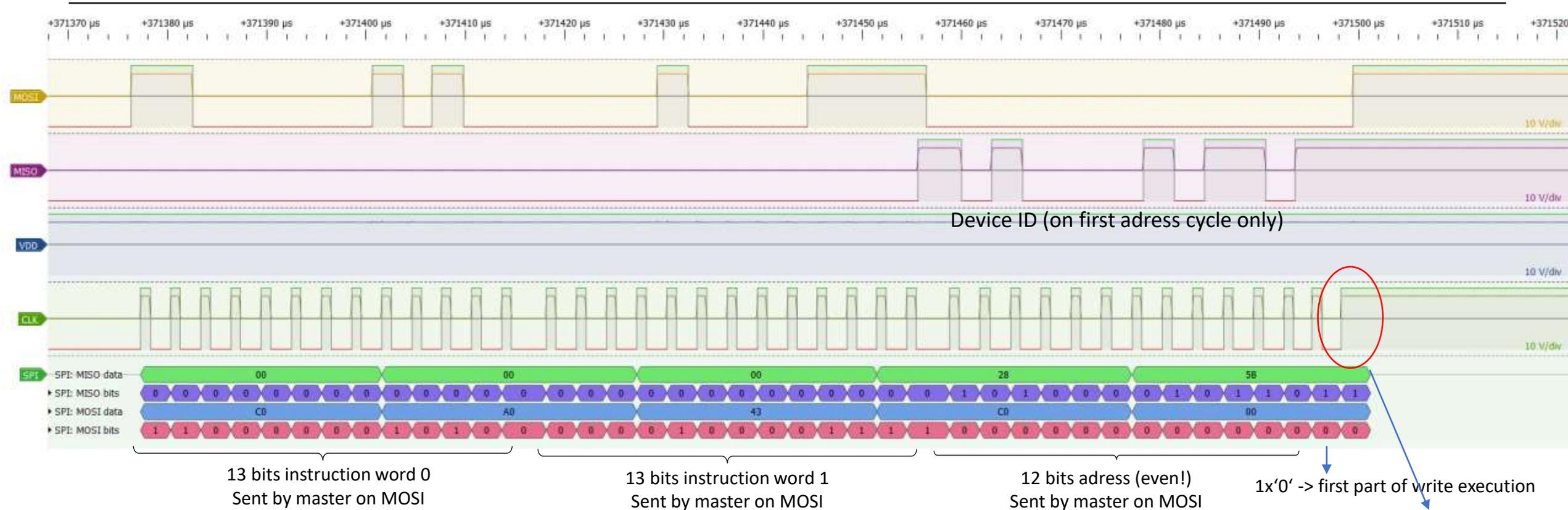
- The entry key is 32 bit and is sent by the master directly after entering programming mode.
- A6 key: 0XA5A5A5A6 -> Initiate reading
- A7 key: 0XA5A5A5A7 -> Initiate writing
- No other codes were found.
- The slave (MCU) pulls MISO down after clock 31. The pin floats before, which could suggest that the programming logic is activated after 31 clocks. This may also suggest that only the LSB is actually used for commands.

Read sequence



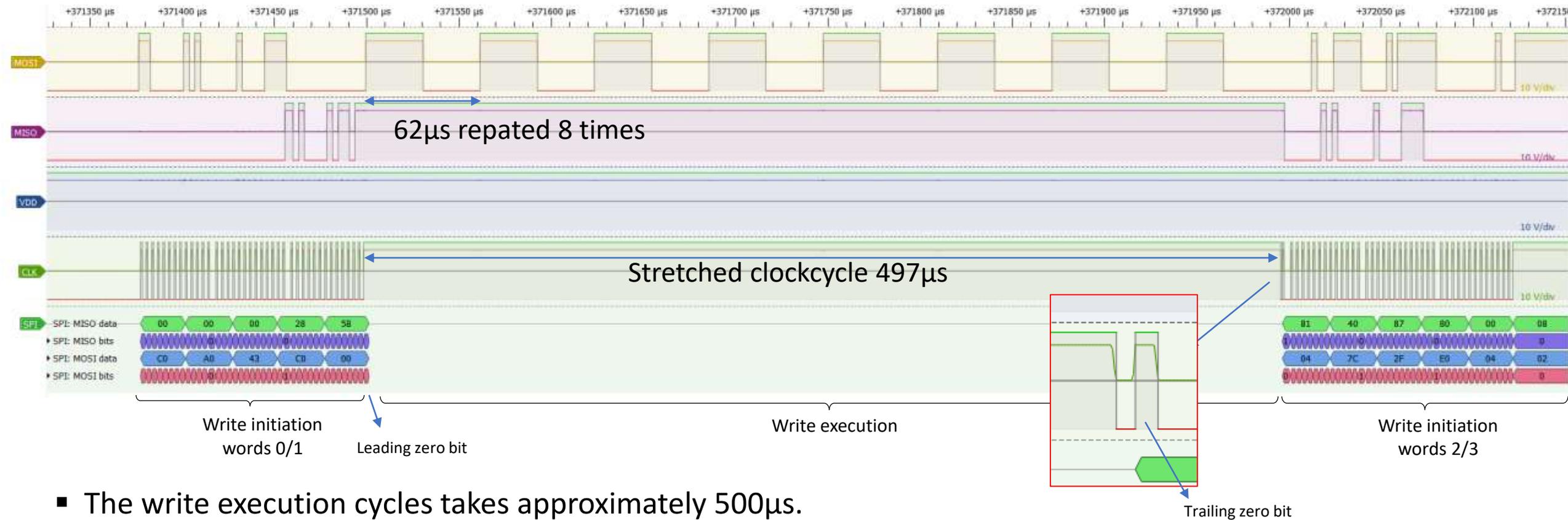
- Read sequence is straight forward:
 - Master sends 12 bit adress, slave sends 13 bits of data in subsequent cycles.
- There is one apparent oddity:
Usually the data on MISO is always updated on the falling clk cycle. However, the MSB of the data is updated with a delay of half a clock cycle, on the rising edge of the clock.
- => For the MSB, it is therefore necessary to set clk high and read MISO after $\sim 2\mu$ s before setting clk low again.
- What is the reason for this behavior? No idea, it could be remnant of a direction switching sequence for a bidirectional port.

Write Sequence Part I



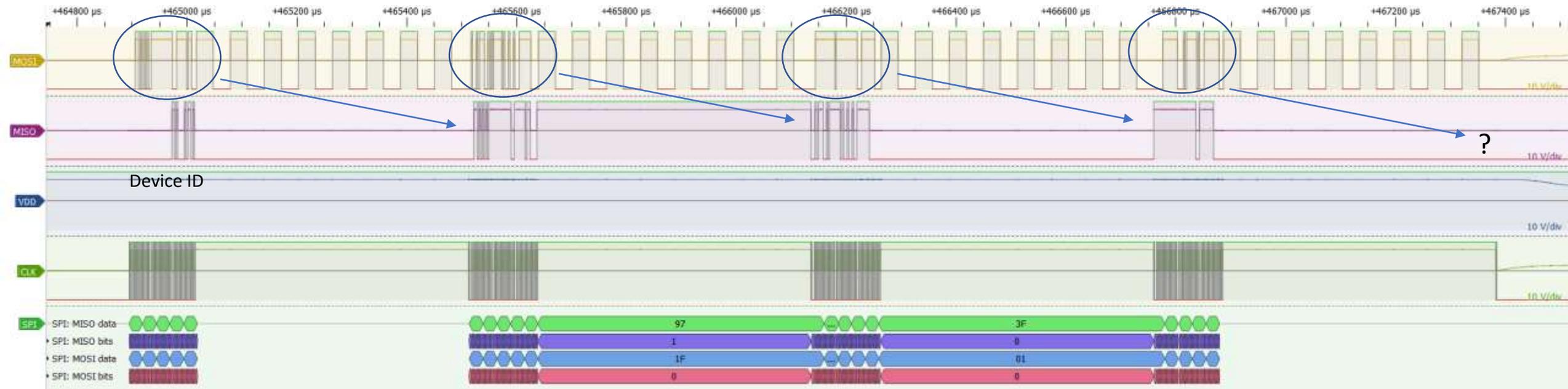
- The PMS150C seems to write two words of memory per write cycle.
- Each write cycle consists of the the following initiation sequence:
 - Send 2x 13 bit instruction words
 - Send 12 bit adress word. (Needs to be dividable by two ?).
 - Send a single „0“ bit. The write cycle seems to be aborted if the device is powered down before sending this bit.
 - The next low-> high transition of the clk seems to initiate the write.

Write Sequence Part II



- The write execution cycles takes approximately 500µs.
 - The sequence consists of three steps:
 - 1) Send 1x'0' at normal clk – „Leading zero bit“
 - 2) Stretched clock cycle (497µs) while MISO is clocked at 16 kHz
 - 3) Send 1x'0' at normal clk – „Trailing zero bit“
 - It appears a secondary clock signal of 16kHz is provided on MISO. Very odd.

Write Sequence Part III – full sequence overview of phase 5



- The last write execution cycle simply ends with the H->L transition of SCLK.
- The MCU will also output data on MISO during the write initiation cycle.
 - First address cycle: The device ID is clocked out.
 - Subsequent cycles: The data and address words of the previous cycle are repeated. This may be a feature to verify the correctness of the written data without a separate read phase. However, it seems that the current software is not making use of it since the information of the last write cycle is discarded.
- Edit: As noted in the EEV forum, this is most likely just information that was clocked out from the SPI register in the the previous cycle.

Revisions

- V0.1 – Jan 7th, 2019 – cpldcpu. Initial report.
- V0.11 - Jan 7th, 2019 – cpldcpu. Updated clean room disclaimer and front matter.
- V0.2 - Jan 8th, 2019 – cpldcpu. Corrected device ID, added pinouts, corrected write mode description.
- V0.3 – Jan 9th, 2019 – cpldcpu. More pinouts, corrected write execution sequence (p.17), updated p.18